

### INCHANGE SEMICONDUCTOR

## isc N-Channel MOSFET Transistor

# FMW30N60S1HF

#### FEATURES

- With TO-247 packaging
- · With low gate drive requirements
- · Low switching loss
- · Low on-state resistance
- · Easy to drive
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### APPLICATIONS

Switching applications

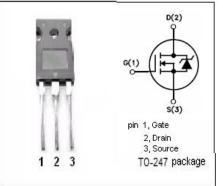
| SYMBOL           | PARAMETER                                  | VALUE    | UNIT |  |  |  |  |  |
|------------------|--|----------|------|--|--|--|--|--|
| V <sub>DSS</sub> | Drain-Source Voltage                       | 600      | V    |  |  |  |  |  |
| V <sub>GSS</sub> | Gate-Source Voltage                        | ±30      | V    |  |  |  |  |  |
| ID               | Drain Current-Continuous@Tc=25℃<br>Tc=100℃ | 30<br>19 | A    |  |  |  |  |  |
| I <sub>DM</sub>  | Drain Current-Single Pulsed                | 90       | А    |  |  |  |  |  |
| PD               | Total Dissipation                          | 220      | W    |  |  |  |  |  |
| Tj               | Operating Junction Temperature             | -55~150  | °C   |  |  |  |  |  |
| T <sub>stg</sub> | Storage Temperature                        | -55~150  | °C   |  |  |  |  |  |

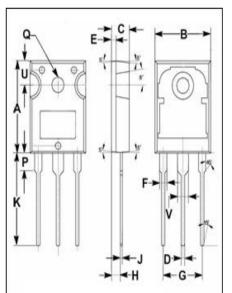
### • ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25℃)

#### • THERMAL CHARACTERISTICS

| SYMBOL    | PARAMETER                          | МАХ  | UNIT |
|-----------|------------------------------------|------|------|
| Rth(ch-c) | Channel-to-case thermal resistance | 0.32 | °C/W |

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### isc website: www.iscsemi.cn



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### **ELECTRICAL CHARACTERISTICS**

#### $T_{C}\text{=}25^{\circ}\!\!\!\mathrm{C}$ unless otherwise specified

| SYMBOL               | PARAMETER                      | CONDITIONS   | MIN | ТҮР | МАХ       | UNIT |
|----------------------|--------------------------------|--|-----|-----|-----------|------|
| BV <sub>DSS</sub>    | Drain-Source Breakdown Voltage | V <sub>GS</sub> =0V; I <sub>D</sub> = 0.25mA   | 600 |     |           | V    |
| V <sub>GS</sub> (th) | Gate Threshold Voltage         | V <sub>DS</sub> =±30V; I <sub>D</sub> =0.25mA  | 2.5 |     | 3.5       | V    |
| R <sub>DS(on)</sub>  | Drain-Source On-Resistance     | V <sub>GS</sub> = 10V; I <sub>D</sub> =15A   |     | 106 | 125       | mΩ   |
| I <sub>GSS</sub>     | Gate-Source Leakage Current    | V <sub>GS</sub> = ±30V;V <sub>DS</sub> =0V   |     |     | ±0.1      | μA   |
| I <sub>DSS</sub>     | Drain-Source Leakage Current   | V <sub>DS</sub> = 600V; V <sub>GS</sub> = 0V;@Tc=25°C<br>V <sub>DS</sub> = 480V; V <sub>GS</sub> = 0V;Tc=125°C |     |     | 25<br>250 | μA   |
| V <sub>SDF</sub>     | Diode forward voltage          | I <sub>SD</sub> =30A, V <sub>GS</sub> = 0V   |     |     | 1.35      | V    |

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